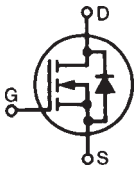
IXYS

X2-Class Power MOSFET

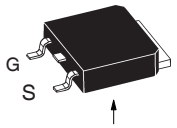
IXTY2N65X2
IXTP2N65X2

V_{DSS} = 650V
I_{D25} = 2A
$R_{DS(on)}$ ≤ 2.3Ω

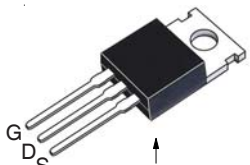
N-Channel Enhancement Mode



TO-252 (IXTY)



TO-220 (IXTP)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	650	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	650	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25°C	2	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	4	A
I_A	T_C = 25°C	1	A
E_{AS}	T_C = 25°C	100	mJ
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	15	V/ns
P_D	T_C = 25°C	55	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
M_d	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in
Weight	TO-252	0.35	g
	TO-220	3.00	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 250μA	650			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250μA	3.0		5.0	V
I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			5	μA
	T_J = 125°C			100	μA
$R_{DS(on)}$	V_{GS} = 10V, $I_D = 0.5 \bullet I_{D25}$, Note 1			2.3	Ω

Features

- International Standard Packages
- Low Q_G
- Avalanche Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

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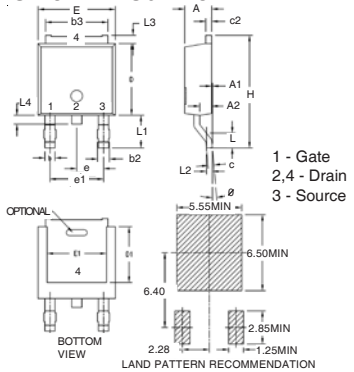
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max
g_{fs}	V_{DS} = 10V, I_D = 0.5 • I_{D25}, Note 1	1.1	1.8	S
R_{Gi}	Gate Input Resistance		14	Ω
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		180	pF
C_{oss}			129	pF
C_{rss}			0.7	pF
	Effective Output Capacitance			
$C_{o(er)}$	Energy related; V_{GS} = 0V		22	pF
$C_{o(tr)}$	Time related; V_{DS} = 0.8 • V_{DSS}		45	pF
$t_{d(on)}$	**Resistive Switching Times**		15	ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		19	ns
$t_{d(off)}$	R_G = 50Ω (External)		20	ns
t_f			14	ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		4.3	nC
Q_{gs}			0.8	nC
Q_{gd}			2.1	nC
R_{thJC}				2.27 °C/W
R_{thCS}	TO-220		0.50	°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
I_S	V_{GS} = 0V			2	A
I_{SM}	Repetitive, pulse Width Limited by T_{JM}			8	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.4	V
t_{rr}	I_F = 1A, -di/dt = 100A/μs		137		ns
Q_{RM}	V_R = 100V		508		nC
I_{RM}			7.4		A

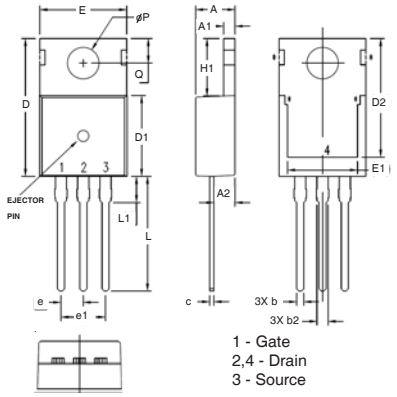
Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

TO-252 AA Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.086	.094	2.19	2.38
A1	0	.005	0	0.12
A2	.038	.046	0.97	1.17
b	.025	.035	0.64	0.89
b2	.030	.045	0.76	1.14
b3	.200	.215	5.08	5.46
c	.018	.024	0.46	0.61
c2	.018	.023	0.46	0.58
D	.235	.245	5.97	6.22
D1	.180	.205	4.57	5.21
E	.250	.265	6.35	6.73
E1	.170	.205	4.32	5.21
e	.090 BSC		2.28 BSC	
e1	.180 BSC		4.57 BSC	
H	.370	.410	9.40	10.42
L	.055	.070	1.40	1.78
L1	.100	.115	2.54	2.92
L2	.020 BSC		0.50 BSC	
L3	.025	.040	0.64	1.02
L4	.025	.040	0.64	1.02
θ	0°	10°	0°	10°

TO-220 Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.169	.185	4.30	4.70
A1	.047	.055	1.20	1.40
A2	.079	.106	2.00	2.70
b	.024	.039	0.60	1.00
b2	.045	.057	1.15	1.45
c	.014	.026	0.35	0.65
D	.587	.626	14.90	15.90
D1	.335	.370	8.50	9.40
(D2)	.500	.531	12.70	13.50
E	.382	.406	9.70	10.30
(E1)	.283	.323	7.20	8.20
e	.100 BSC		2.54 BSC	
e1	.200 BSC		5.08 BSC	
H1	.244	.268	6.20	6.80
L	.492	.547	12.50	13.90
L1	.110	.154	2.80	3.90
ØP	.134	.150	3.40	3.80
Q	.106	.126	2.70	3.20

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123B1 6,306,728B1 6,404,065B1 6,534,343 6,583,505 6,683,344 6,710,405B2 6,710,463 6,727,585 6,759,692 6,771,478B2 7,005,734B2 7,063,975B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25°C

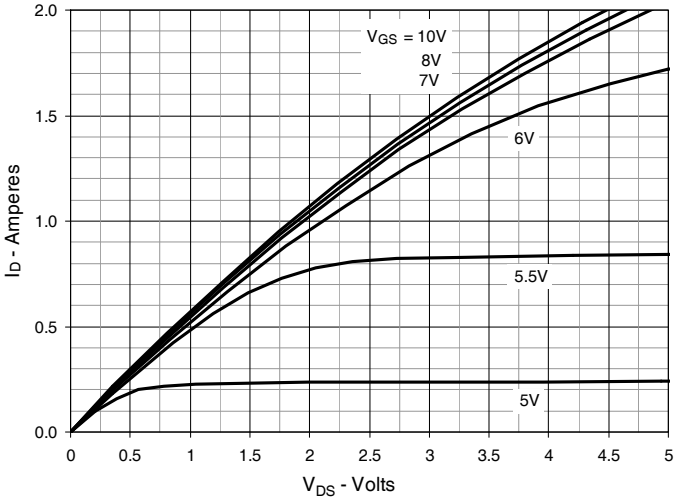


Fig. 2. Extended Output Characteristics @ T_J = 25°C

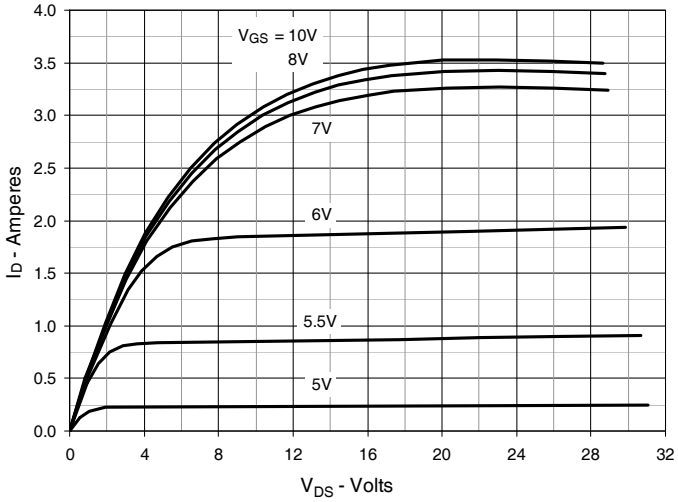


Fig. 3. Output Characteristics @ T_J = 125°C

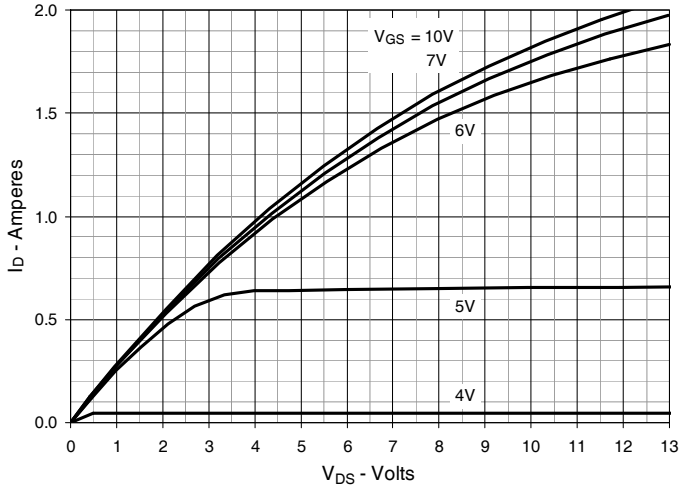


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 1A Value vs. Junction Temperature

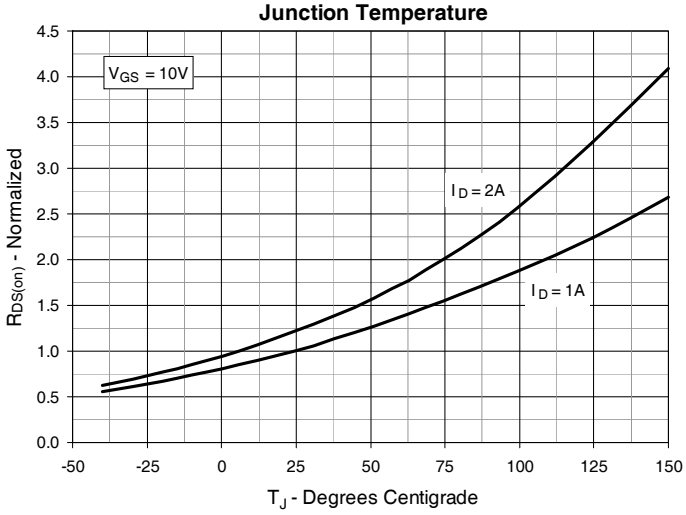


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 1A Value vs. Drain Current

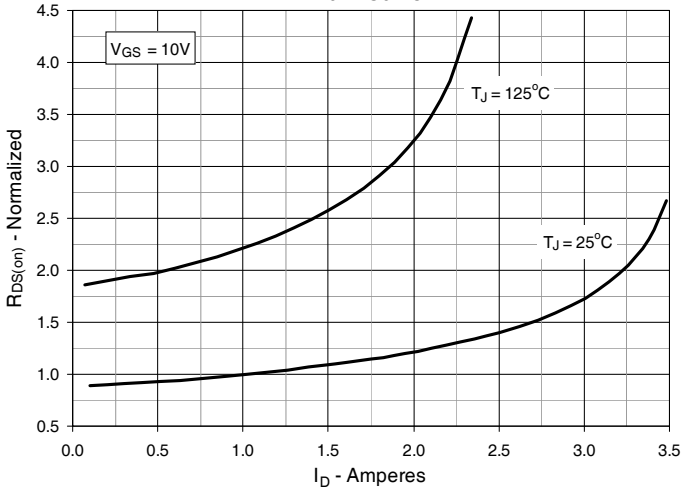
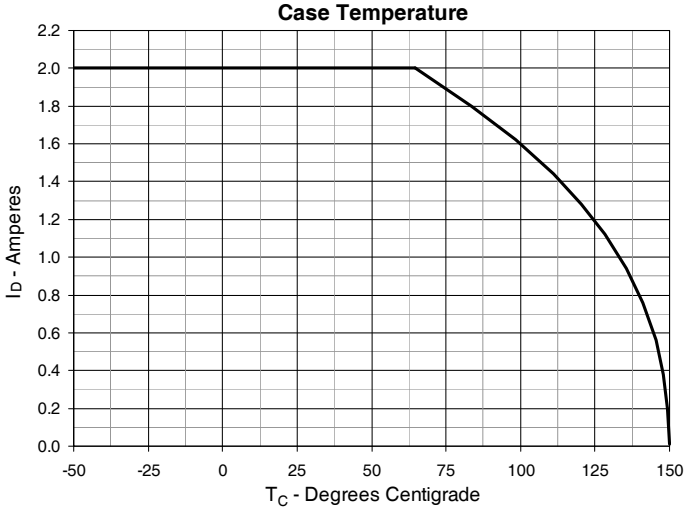


Fig. 6. Maximum Drain Current vs. Case Temperature



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Fig. 7. Input Admittance

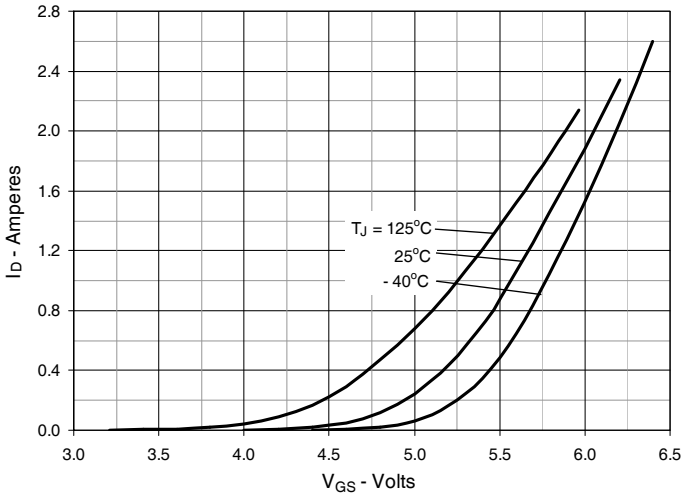


Fig. 8. Transconductance

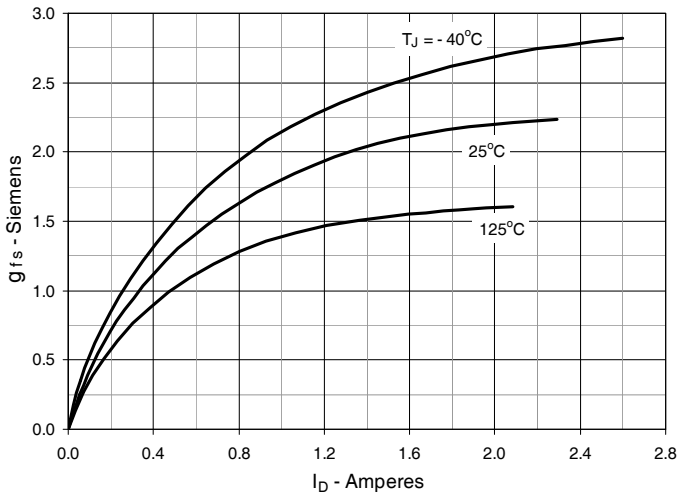


Fig. 9. Forward Voltage Drop of Intrinsic Diode

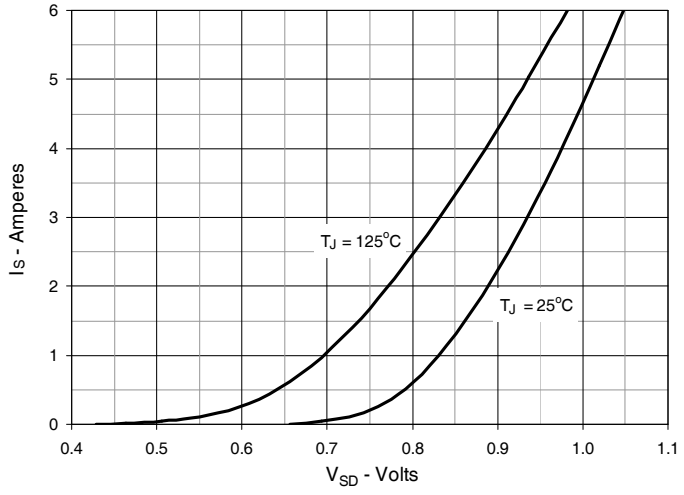


Fig. 10. Gate Charge

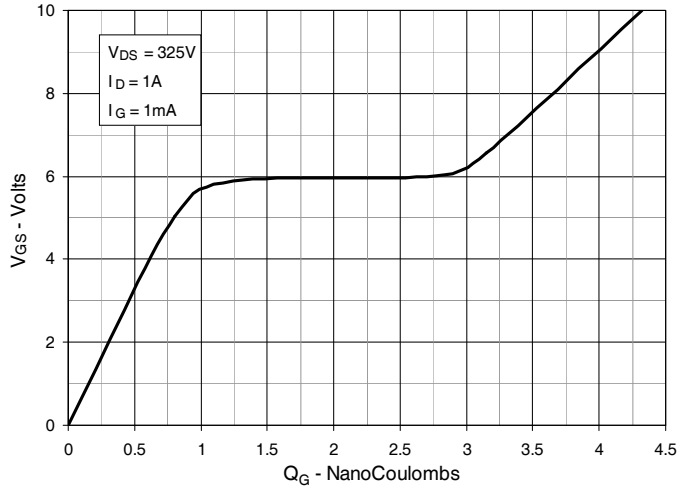


Fig. 11. Capacitance

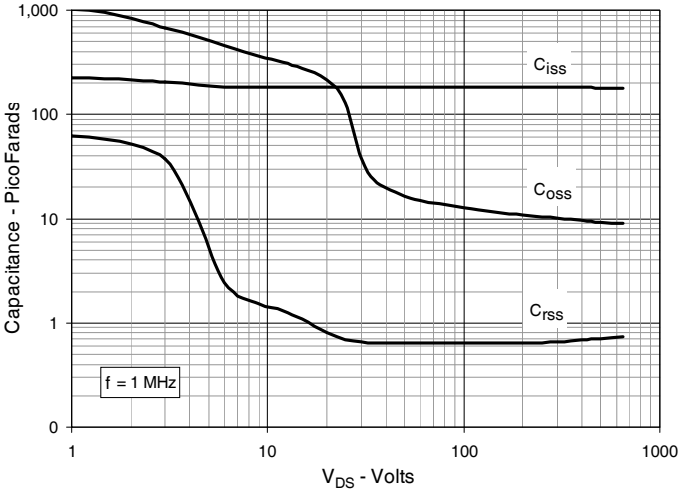
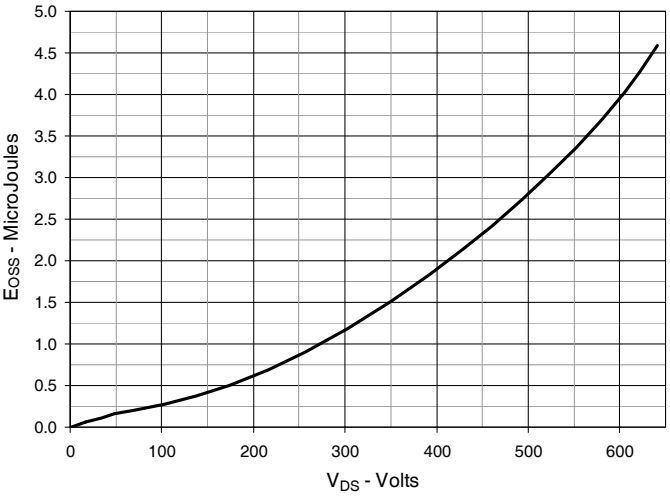


Fig. 12. Output Capacitance Stored Energy



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Fig. 13. Forward-Bias Safe Operating Area

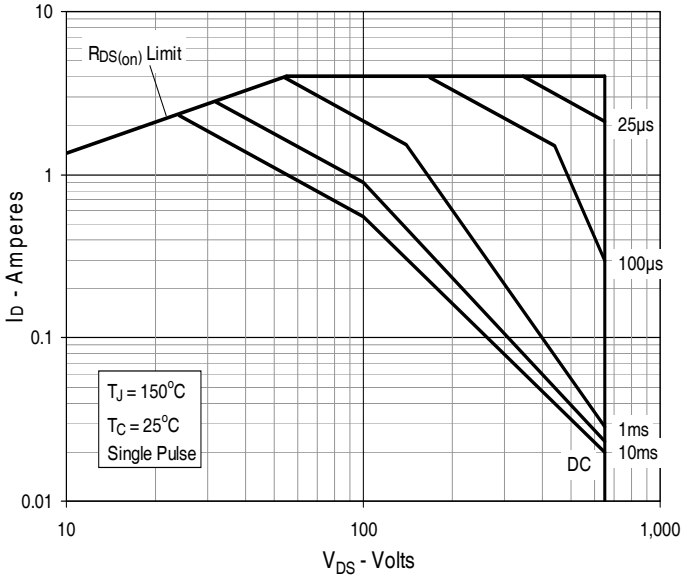
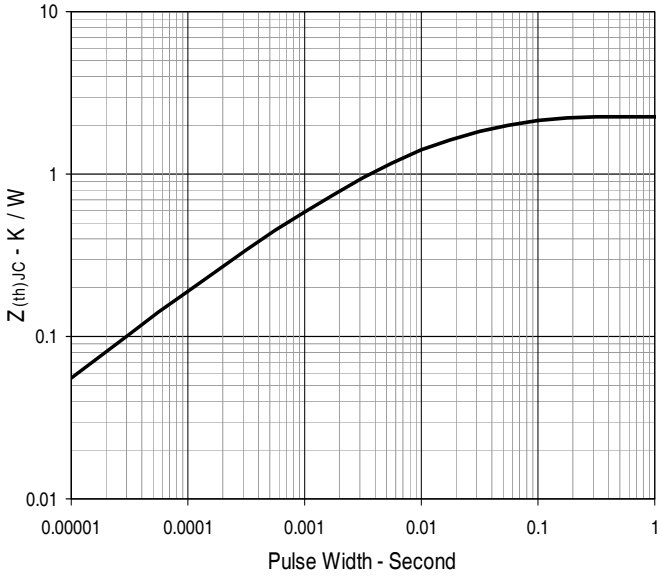


Fig. 14. Maximum Transient Thermal Impedance



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